

CMLD3003DO
CMLD3003DOG

SURFACE MOUNT SILICON
DUAL, ISOLATED, OPPOSING
LOW LEAKAGE
SWITCHING DIODES



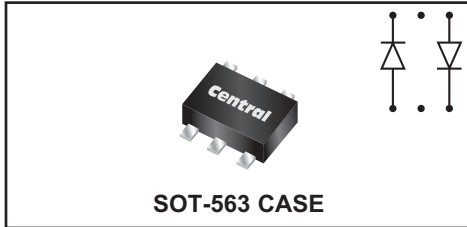
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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD3003DO and CMLD3003DOG devices contain two (2) isolated opposing configuration, silicon switching diodes, manufactured by the epitaxial planar process, epoxy molded in an SOT-563 surface mount package. These devices are designed for switching applications requiring extremely low leakage.

MARKING CODES:

CMLD3003DO: C30
CMLD3003DOG: 3CG



SOT-563 CASE

• The CMLD3003DOG is *Halogen Free* by design

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage	V_R	180	V
Average Rectified Current	I_O	200	mA
Continuous Forward Current	I_F	600	mA
Peak Repetitive Forward Current	I_{FRM}	700	mA
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$	I_{FSM}	2.0	A
Peak Forward Surge Current, $t_p=1.0\text{s}$	I_{FSM}	1.0	A
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	500	$^\circ\text{C/W}$

SYMBOL

V_R	180	V
I_O	200	mA
I_F	600	mA
I_{FRM}	700	mA
I_{FSM}	2.0	A
I_{FSM}	1.0	A
P_D	250	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	500	$^\circ\text{C/W}$

UNITS

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=125\text{V}$		1.0	nA
I_R	$V_R=125\text{V}, T_A=150^\circ\text{C}$		3.0	μA
I_R	$V_R=180\text{V}$		10	nA
I_R	$V_R=180\text{V}, T_A=150^\circ\text{C}$		5.0	μA
BV_R	$I_R=5.0\mu\text{A}$	200		V
V_F	$I_F=1.0\text{mA}$	0.62	0.72	V
V_F	$I_F=10\text{mA}$	0.72	0.83	V
V_F	$I_F=50\text{mA}$	0.80	0.89	V
V_F	$I_F=100\text{mA}$	0.83	0.93	V
V_F	$I_F=200\text{mA}$	0.87	1.10	V
V_F	$I_F=300\text{mA}$	0.90	1.15	V
C_J	$V_R=0, f=1.0\text{MHz}$		4.0	pF

R4 (15-June 2015)